

# **BC212L**



**TO-92** 

# **PNP General Purpose Amplifier**

This device is designed for general purpose amplifier applications at collector currents to 300mA. Sourced from Process 68.

Absolute Maximum Ratings\* TA=

T<sub>A = 25°C</sub> unless otherwise noted

-			
Symbol	Parameter	Value	Units
V <sub>CEO</sub>	Collector-Emitter Voltage	50	V
V <sub>CBO</sub>	Collector-Base Voltage	60	V
V <sub>EBO</sub>	Emitter-Base Voltage	5	V
I <sub>C</sub>	Collector Current - Continuous	300	mA
T <sub>J, Tstg</sub>	Operating and Storage Junction Temperature Range	-55 to +150	°C

 $<sup>^{\</sup>star}$ These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

### NOTES:

- 1) These ratings are based on a maximum junction temperature of 150  $^{\circ}\text{C}.$
- 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

## Thermal Characteristics T<sub>A = 25°C unless otherwise noted</sub>

Symbol	Characteristic	Max	Units
P <sub>D</sub>	Total Device Dissipation Derate above 25°C	625 5.0	mW mW/°C
R <sub>θ</sub> JC	Thermal Resistance, Junction to Case		°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient	200	°C/W

PNP	General	Purpose	Amplifier

(continued)

# **Electrical Characteristics**

T<sub>A = 25°C</sub> unless otherwise noted

Symbol	Parameter	Test Conditions	Min	Max	Units
OFF CHA	RACTERISTICS				
BV <sub>CEO</sub>	Collector-Emitter Breakdown Voltage	I <sub>C</sub> = 2 mA	50		V
BV <sub>CBO</sub>	Collector-Base Breakdown Voltage	I <sub>C</sub> = 10 μA	60		V
BV <sub>EBO</sub>	Emitter-Base Breakdown Voltage	ΙΕ = 10 μΑ	5		V
СВО	Collector Cutoff Current	V <sub>CB</sub> = 30V		15	nA
EBO	Emitter Cutoff Current	V <sub>EB</sub> = 4V		15	nA
ON CHAR	ACTERISTICS*				•
JEE	DC Current Gain	$I_C = 10 \text{ uA}, V_{CE} = 5 \text{ V}$ $I_C = 2 \text{ mA}, V_{CE} = 5 \text{ V}$	40 60	300	
√ <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5 mA		0.6	V
/ <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	I <sub>C</sub> = 100 mA, I <sub>B</sub> = 5 mA		1.1	V
/ <sub>BE(on)</sub>	Base-Emitter On Voltage	I <sub>C</sub> = 2 mA, V <sub>CE</sub> = 5 V	0.6	0.72	V
SMALL S	IGNAL CHARACTERISTICS		1		
C <sub>ob</sub>	Output Capacitance	V <sub>CB</sub> = 10 V, f = 1.0 MHz		10	pF
η <sub>fe</sub>	Small Signal Current Gain	I <sub>C</sub> = 2 mA,V <sub>CE</sub> = 5 V, f=1kHz	60		-
NF	Noise Figure	I <sub>C</sub> = 200 uA,V <sub>CE</sub> = 5 V, f=1kHz, Rg=2KOhms,BW=200Hz		10	dB
Т	Current Gain-Bandwidth Product	VCE=5V, IC=10mA,f=100MHz	200		MHz

\*Pulse Test: Pulse Width < 300 $\mu$ s, Duty Cycle < 2.0%

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